



RECTRON

SEMICONDUCTOR

TECHNICAL SPECIFICATION

SD4150

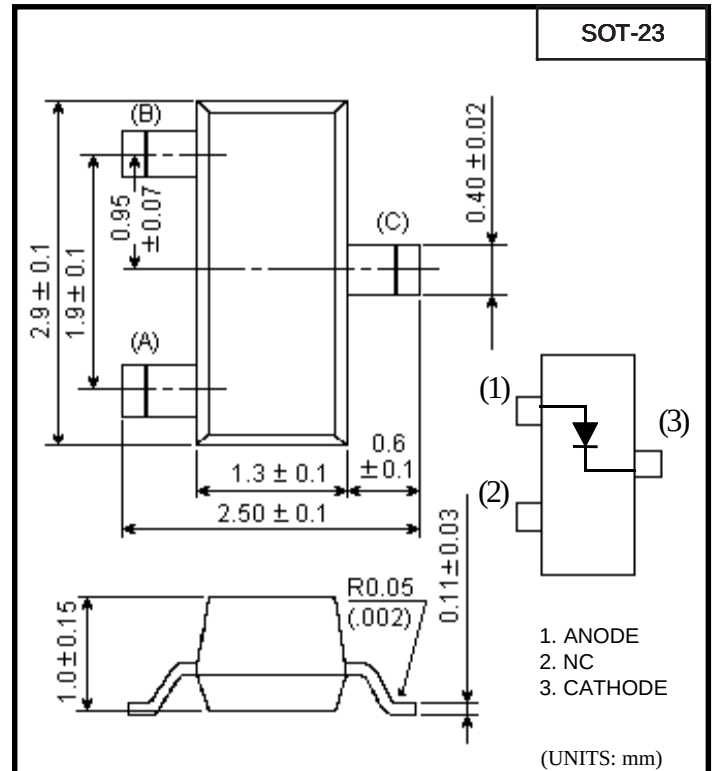
SURFACE MOUNT 1N4150 DIODE

Absolute Maximum Ratings (Ta=25°C)

ITEMS	SYMBOL	RATINGS	UNIT
Reverse Voltage	VR	50	V
Reverse Recovery Time	trr	6	ns
Forward Voltage @ If = 50 mA	VF	0.86	V
Forward Current	IF	300	mA
Junction Temp.	Tj	-55 to 150	°C
Storage Temp.	Tstg	-55 to 150	°C

Mechanical Data

ITEMS	MATERIALS
Package	SOT-23
Lead Frame	42 Alloy
Lead Finish	Solder Plating
Bond Wire	Au
Mold Resin	Epoxy
Chip	Silicon



Electrical Characteristics (Ta=25°C)

RATINGS	SYMBOL	RATINGS	UNIT
Reverse Voltage IR= 100uA	VR	50	V
Repetitive Peak Reverse Voltage	VRRM	75	V
Repetitive Peak Forward Current	IFRM	600	mA
Forward Voltage IF= 1mA IF= 10mA IF= 50mA IF= 100mA IF= 200mA	VF	0.62 0.74 0.86 0.92 1.00	V
Reverse Current VR= 50V VR= 50V (Tj= 150°C)	IR	0.10 100	uA
Junction Capacitance VR = 0 V, f = 1MHz	Cj	2.5	pF

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